



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Product Summary

Device	BV _{DSS}	R _{DS(ON)}		I _D T _A = +25°C
Q1	30V	60mΩ @ V _{GS} = 10V		3.6A
		100mΩ @ V _{GS} = 4.5V		2.7A
Q2	-30V	95mΩ @ V _{GS} = -10V		-2.8A
		140mΩ @ V _{GS} = -4.5V		-2.3A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

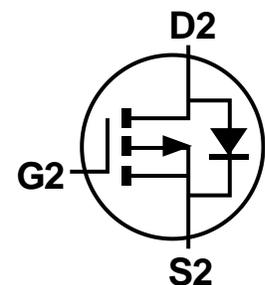
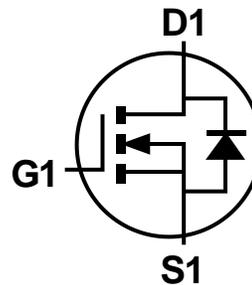
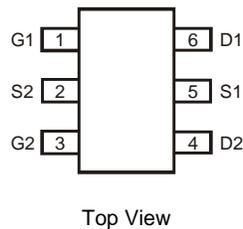
- Backlighting
- DC-DC Converters
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.013 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Q1 Value	Q2 Value	Unit
Drain-Source Voltage			V_{DSS}	30	-30	V
Gate-Source Voltage			V_{GSS}	± 12	± 12	V
Continuous Drain Current (Note 6) N-Channel: $V_{GS} = 4.5\text{V}$ P-Channel: $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	3.6	-2.8	A
		$T_A = +70^\circ\text{C}$		2.8	-2.2	
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.1	-1.0	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	16	-16	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.83	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	151	$^\circ\text{C/W}$
Power Dissipation (Note 6)	P_D	1.16	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6)	$R_{\theta JA}$	108	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_L, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics – Q1 N-Channel (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.7	1.0	1.8	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	42	60	m Ω	$V_{GS} = 10\text{V}, I_D = 3.1\text{A}$
			45	100		$V_{GS} = 4.5\text{V}, I_D = 2\text{A}$
			48	150		$V_{GS} = 3.3\text{V}, I_D = 1.5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.8	1	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	395	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.2\text{MHz}$
Output Capacitance	C_{oss}	—	39	—		
Reverse Transfer Capacitance	C_{rss}	—	26	—		
Gate Resistance	R_g	—	3.1	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	5.6	—	nC	$V_{DS} = 15\text{V}, V_{GS} = 4.5\text{V}, I_D = 3.1\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	11.3	—		
Gate-Source Charge	Q_{gs}	—	0.2	—		
Gate-Drain Charge	Q_{gd}	—	1.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.8	—	ns	$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, R_G = 3\Omega, R_L = 4.7\Omega$
Turn-On Rise Time	t_R	—	30.8	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.3	—		
Turn-Off Fall Time	t_F	—	2.7	—		

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

Electrical Characteristics – Q2 P-Channel (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.7	-1.1	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	60	95	mΩ	V _{GS} = -10V, I _D = -2.7A
			81	140		V _{GS} = -4.5V, I _D = -1.5A
			104	300		V _{GS} = -3.3V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	324	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.2MHz
Output Capacitance	C _{oss}	—	44	—		
Reverse Transfer Capacitance	C _{rss}	—	33	—		
Gate Resistance	R _g	—	7.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	4.4	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -3A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	8.6	—		
Gate-Source Charge	Q _{gs}	—	0.3	—		
Gate-Drain Charge	Q _{gd}	—	1.5	—		
Turn-On Delay Time	t _{D(ON)}	—	7.7	—	ns	V _{GS} = -10V, V _{DS} = -15V, R _G = 6Ω, R _L = 15Ω
Turn-On Rise Time	t _R	—	17.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	17.8	—		
Turn-Off Fall Time	t _F	—	29.5	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

Typical Characteristics – N-Channel

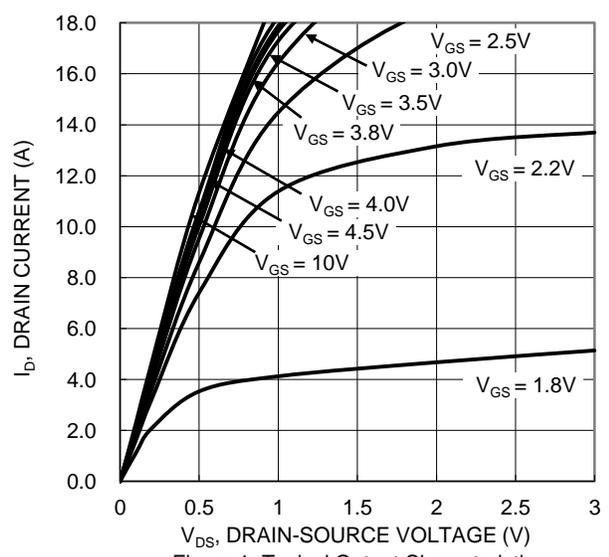


Figure 1. Typical Output Characteristic

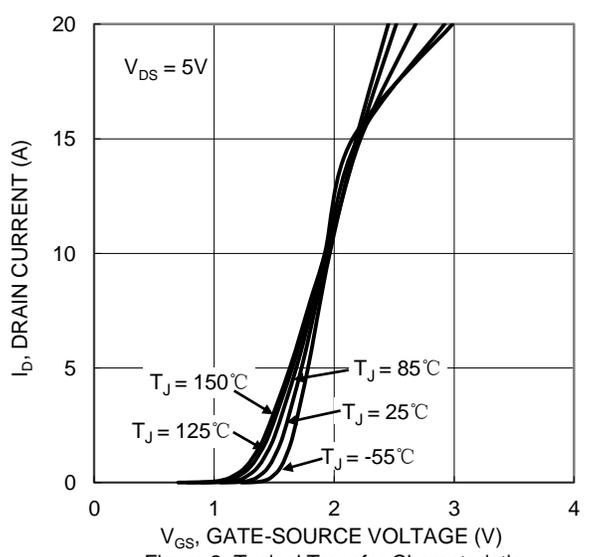


Figure 2. Typical Transfer Characteristic

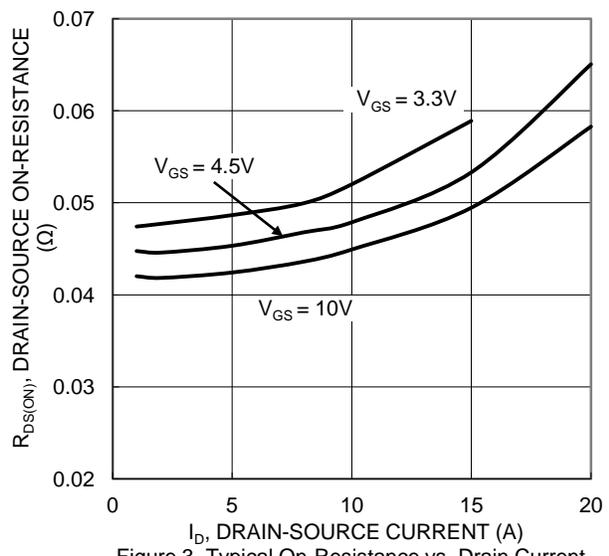


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

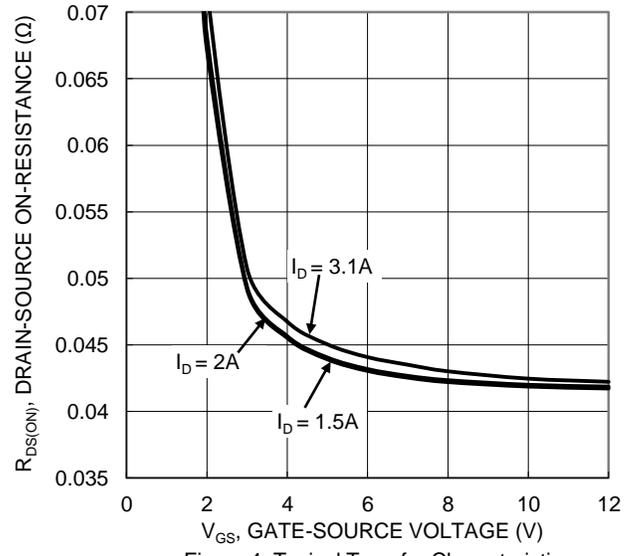


Figure 4. Typical Transfer Characteristic

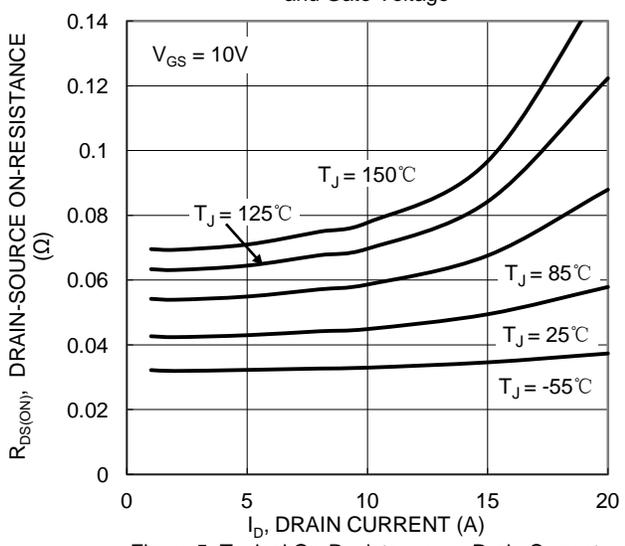


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

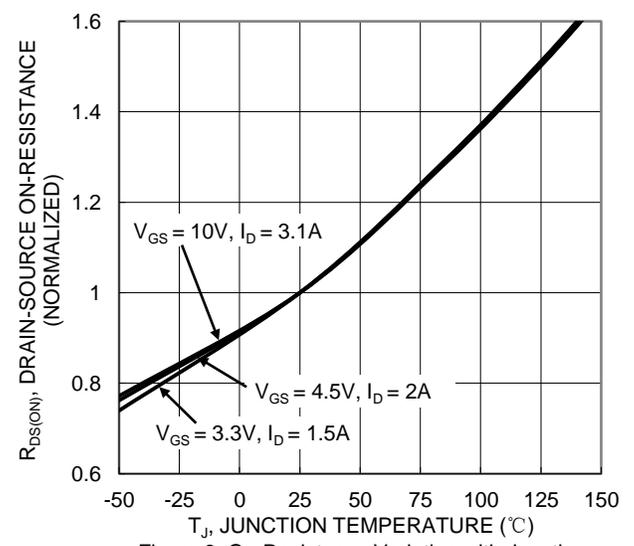


Figure 6. On-Resistance Variation with Junction Temperature

Typical Characteristics – N-Channel (continued)

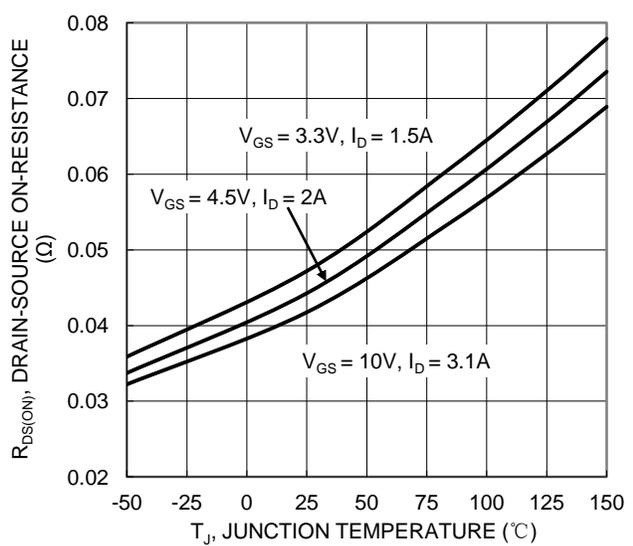


Figure 7. On-Resistance Variation with Junction Temperature

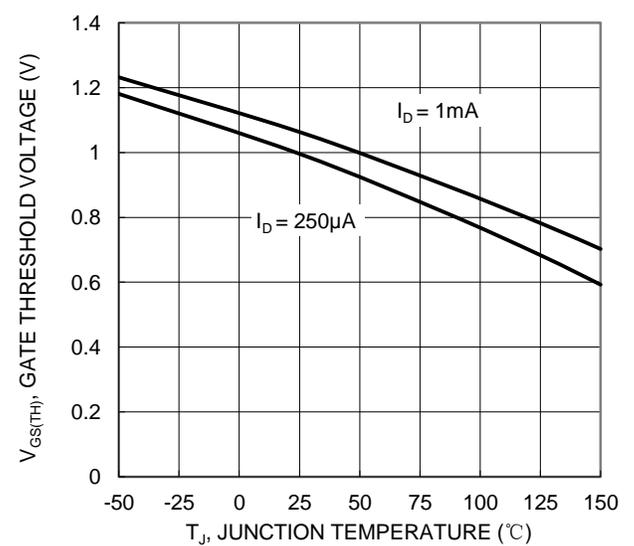


Figure 8. Gate Threshold Variation vs. Junction Temperature

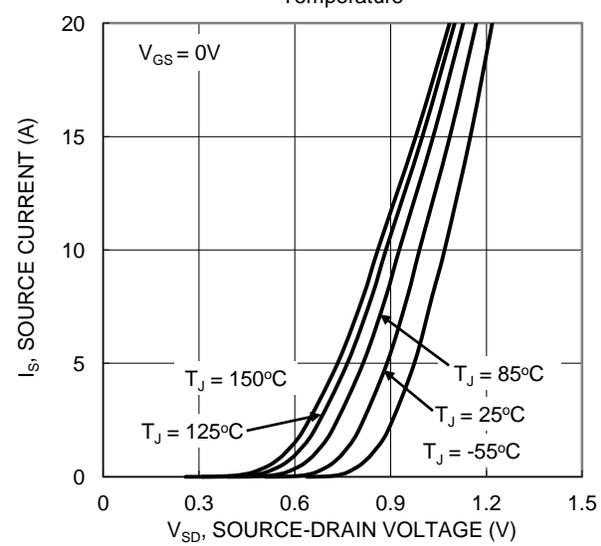


Figure 9. Diode Forward Voltage vs. Current

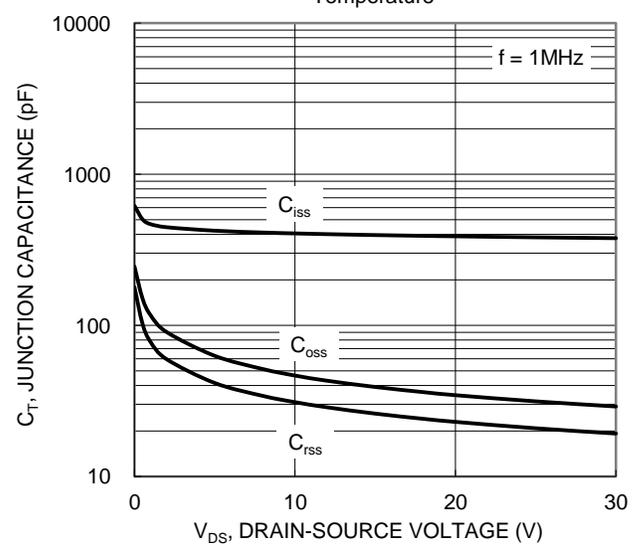


Figure 10. Typical Junction Capacitance

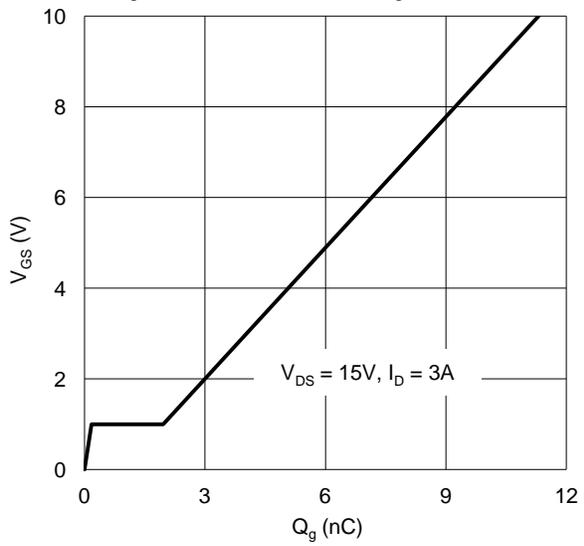


Figure 11. Gate Charge

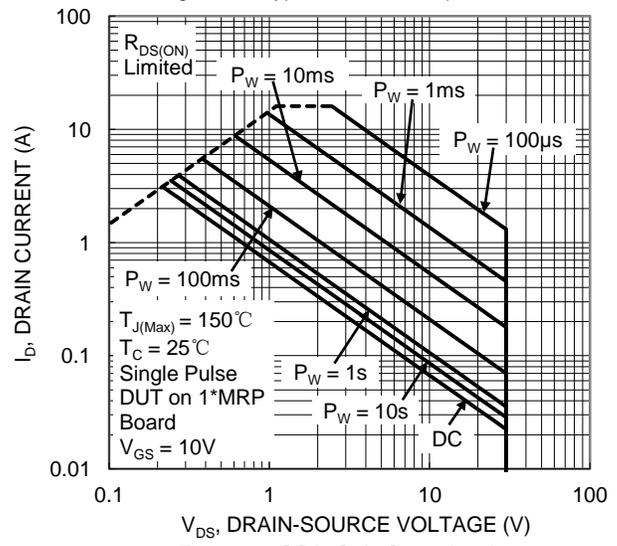


Figure 12. SOA, Safe Operation Area

Typical Characteristics – P-Channel

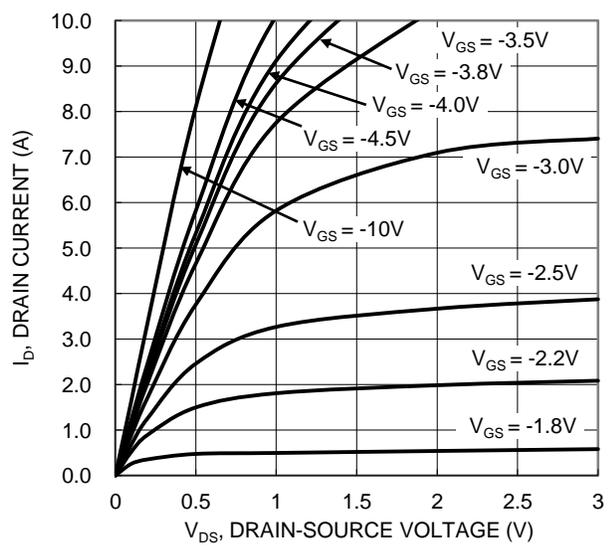


Figure 13. Typical Output Characteristic

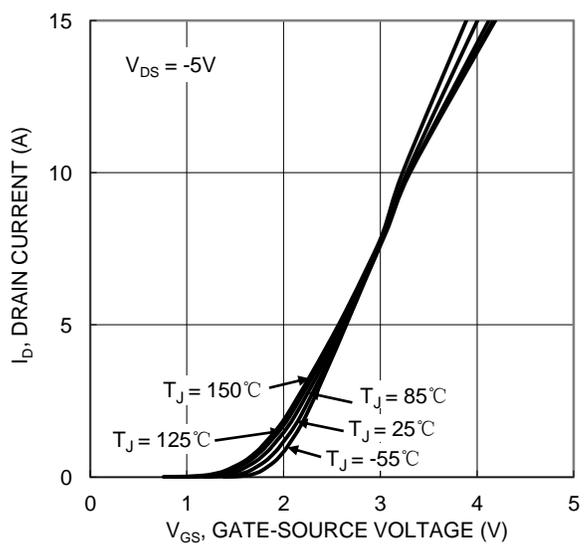


Figure 14. Typical Transfer Characteristic

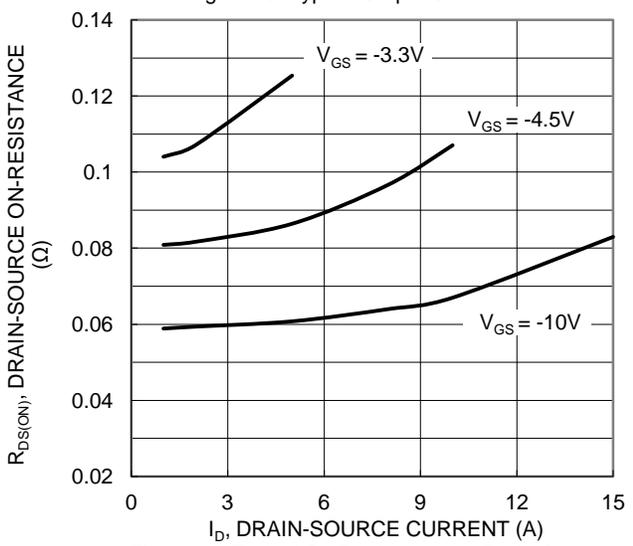


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

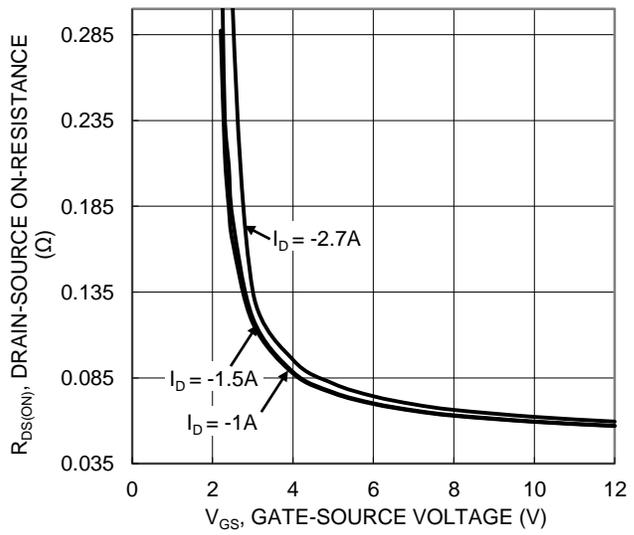


Figure 16. Typical Transfer Characteristic

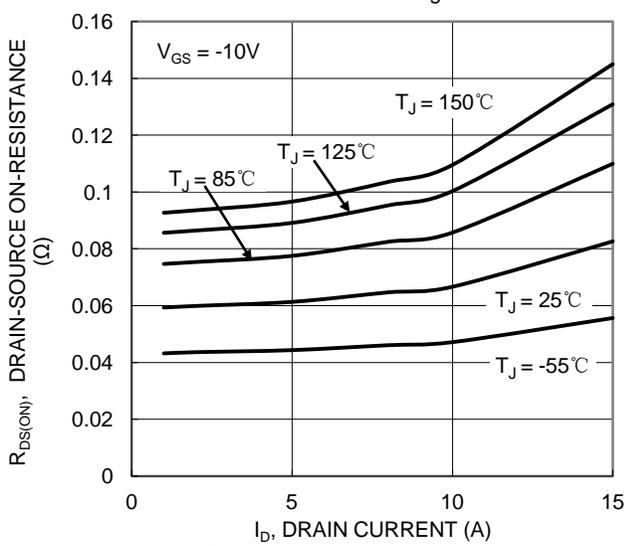


Figure 17. Typical On-Resistance vs. Drain Current and Junction Temperature

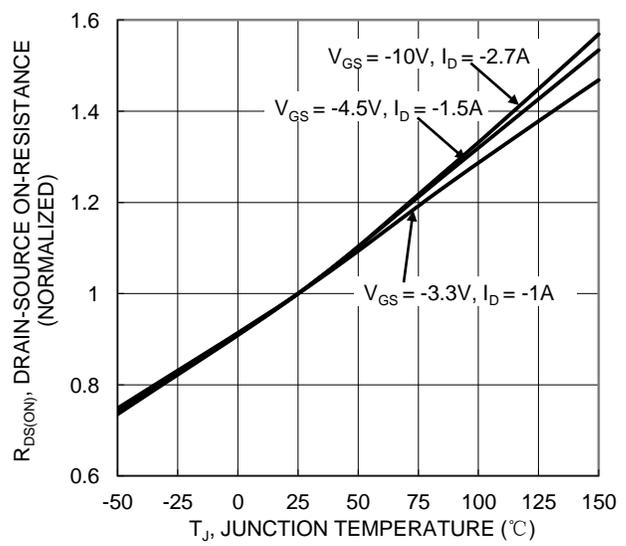


Figure 18. On-Resistance Variation with Junction Temperature

Typical Characteristics – P-Channel (continued)

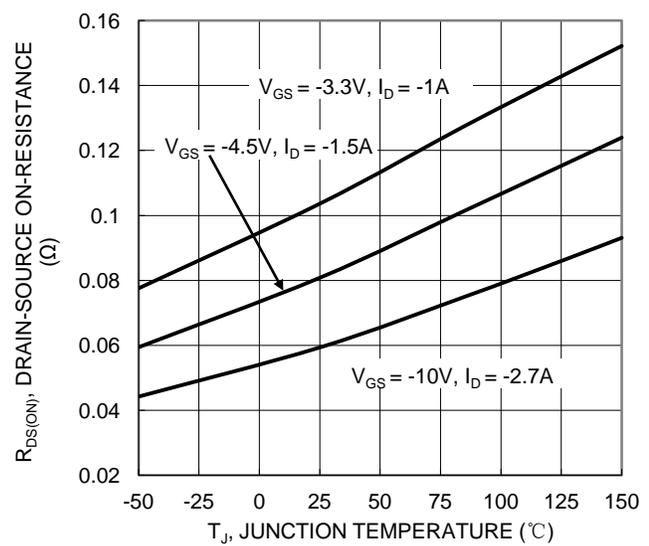


Figure 19. On-Resistance Variation with Junction Temperature

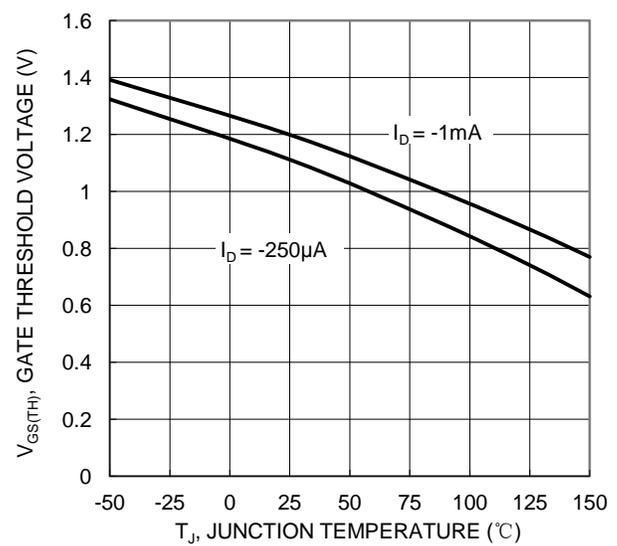


Figure 20. Gate Threshold Variation vs. Junction Temperature

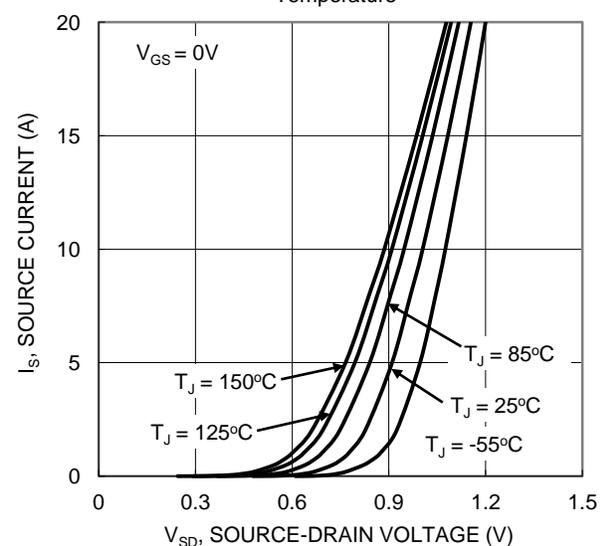


Figure 21. Diode Forward Voltage vs. Current

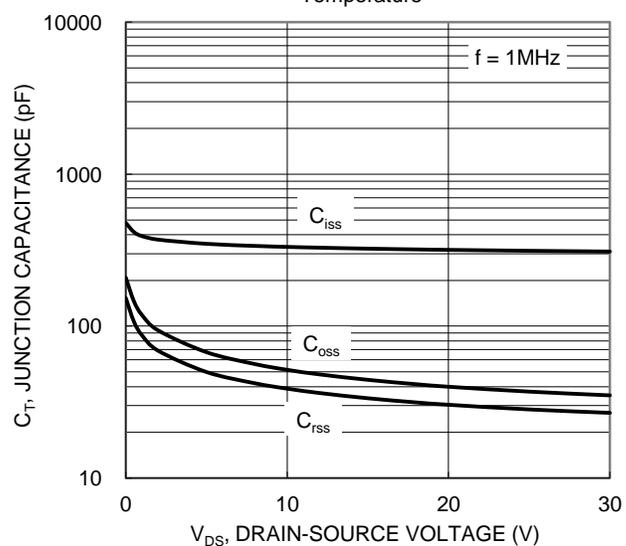


Figure 22. Typical Junction Capacitance

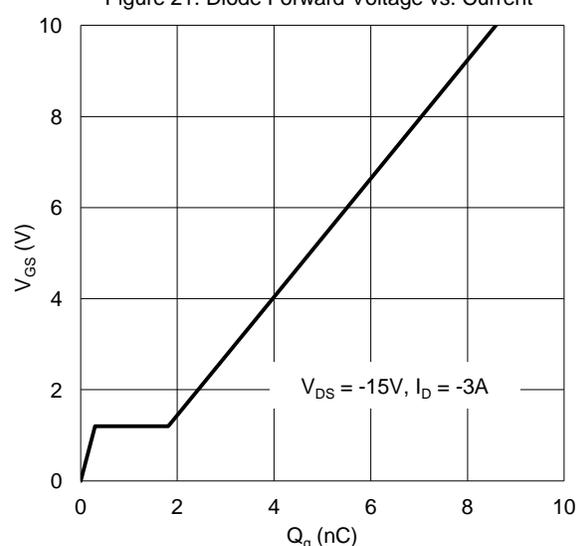


Figure 23. Gate Charge

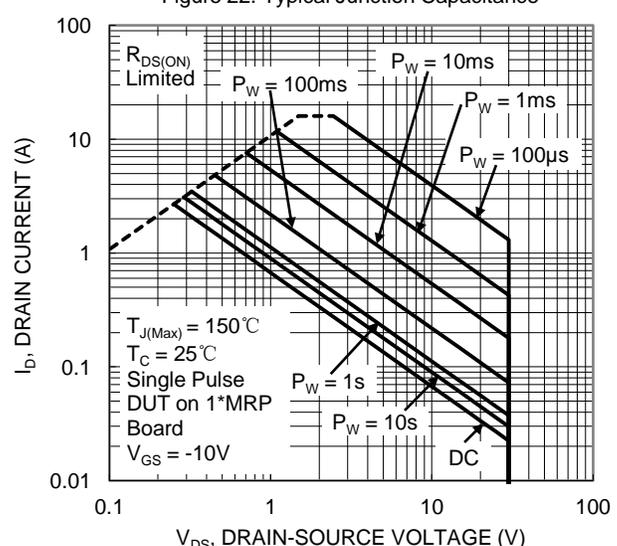


Figure 24. SOA, Safe Operation Area

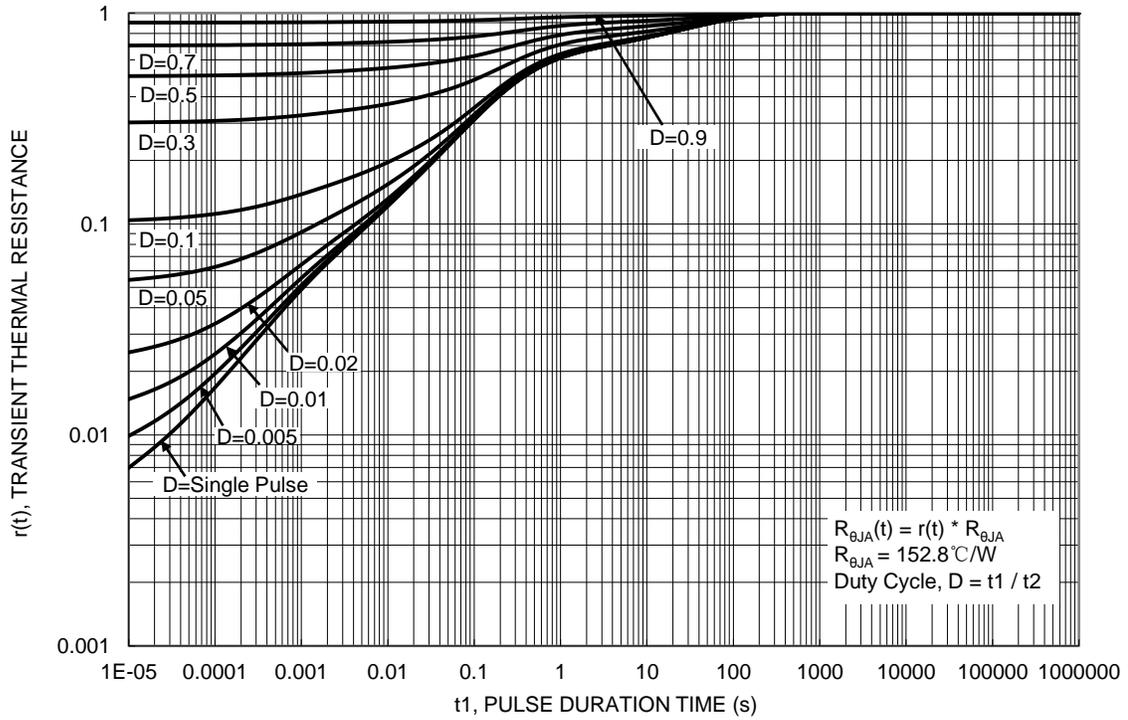
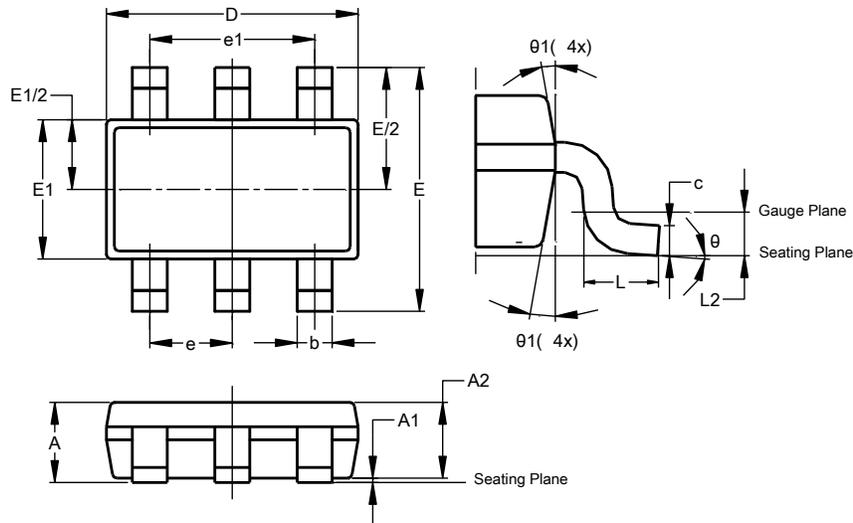


Figure 25. Transient Thermal Resistance

Package Outline Dimensions

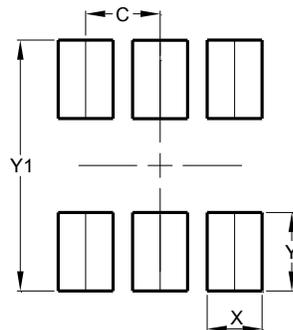
TSOT26



TSOT26			
Dim	Min	Max	Typ
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199